

2N60K-TA

Power MOSFET

2A, 600V N-CHANNEL
POWER MOSFET

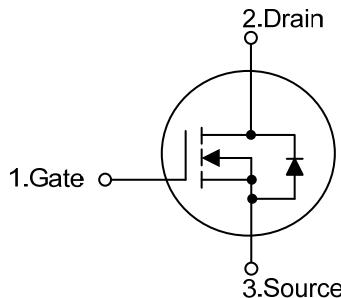
■ DESCRIPTION

The UTC **2N60K-TA** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

- * $R_{DS(ON)} < 5.0\Omega$ @ $V_{GS} = 10V$, $I_D = 1A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

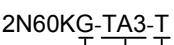
■ SYMBOL



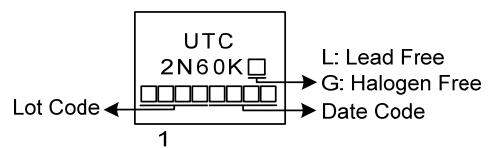
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N60KL-TA3-T	2N60KG-TA3-T	TO-220	G	D	S	Tube
2N60KL-TF3-T	2N60KG-TF3-T	TO-220F	G	D	S	Tube
2N60KL-TF1-T	2N60KG-TF1-T	TO-220F1	G	D	S	Tube
2N60KL-TF2-T	2N60KG-TF2-T	TO-220F2	G	D	S	Tube
2N60KL-TF3T-T	2N60KG-TF3T-T	TO-220F3	G	D	S	Tube
2N60KL-TM3-T	2N60KG-TM3-T	TO-251	G	D	S	Tube
2N60KL-TMS-T	2N60KG-TMS-T	TO-251S	G	D	S	Tube
2N60KL-TN3-R	2N60KG-TN3-R	TO-252	G	D	S	Tape Reel
2N60KL-TND-R	2N60KG-TND-R	TO-252D	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

 (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TF3T: TO-220F3, TM3: TO-251 TMS: TO-251S, TN3: TO-252, TND: TO-252D (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Drain-Source Voltage	V_{DSS}	600	V	
Gate-Source Voltage	V_{GSS}	± 30	V	
Avalanche Current (Note 2)	I_{AR}	2.0	A	
Drain Current	Continuous	I_D	2.0	A
	Pulsed (Note 2)	I_{DM}	8.0	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	85	mJ
	Repetitive (Note 2)	E_{AR}	4.5	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns	
Power Dissipation	TO-220	P_D	54	W
	TO-220F/TO-220F1		21	W
	TO-220F3		23	W
	TO-220F2		44	W
	TO-251/TO-251S			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L=42.5\text{mH}$, $I_{AS}=2.0\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 2.4\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C/W}$
		100	$^\circ\text{C/W}$
Junction to Case	θ_{JC}	2.32	$^\circ\text{C/W}$
		5.95	$^\circ\text{C/W}$
		5.43	$^\circ\text{C/W}$
		2.87	$^\circ\text{C/W}$

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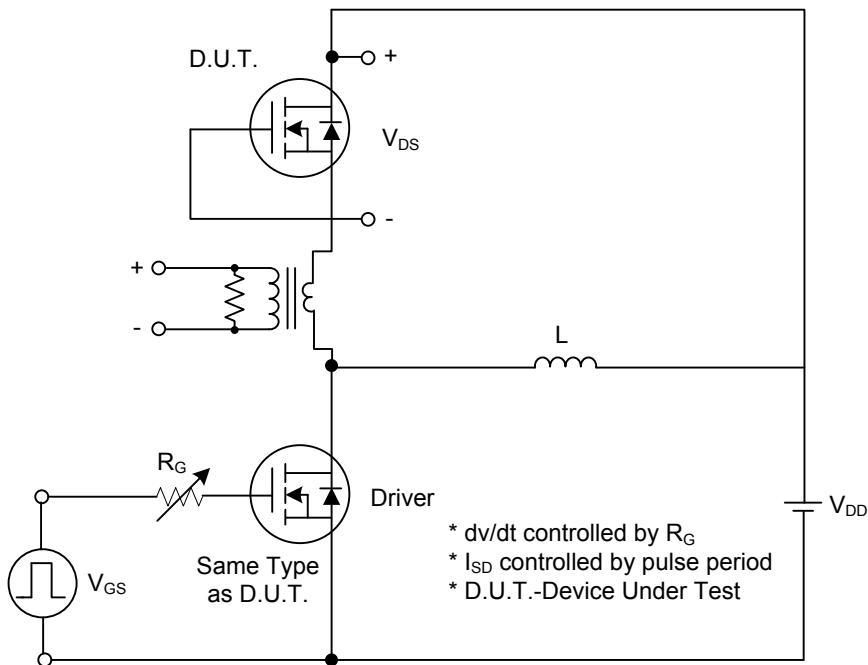
■ ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	600			V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}} = 600\text{V}, V_{\text{GS}} = 0\text{V}$			10	μA
		$V_{\text{DS}} = 480\text{V}, T_c = 125^\circ\text{C}$			100	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}} = 30\text{V}, V_{\text{DS}} = 0\text{V}$			100	nA
		$V_{\text{GS}} = -30\text{V}, V_{\text{DS}} = 0\text{V}$			-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	$I_{\text{D}} = 250\mu\text{A}$, Referenced to 25°C		0.4		$\text{V}/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{\text{GS(TH)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 1\text{A}$		4.0	5.0	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{\text{DS}} = 25\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		205	290	pF
Output Capacitance	C_{OSS}			40	45	pF
Reverse Transfer Capacitance	C_{RSS}			16	20	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{\text{D(ON)}}$	$V_{\text{DD}} = 30\text{V}, I_{\text{D}} = 0.5\text{A}, R_{\text{G}} = 25\Omega$ (Note 1, 2)		23	40	ns
Turn-On Rise Time	t_{R}			40	50	ns
Turn-Off Delay Time	$t_{\text{D(OFF)}}$			80	100	ns
Turn-Off Fall Time	t_{F}			40	55	ns
Total Gate Charge	Q_{G}	$V_{\text{DS}} = 50\text{V}, V_{\text{GS}} = 1.0\text{V}, I_{\text{D}} = 1.3\text{A}$ (Note 1, 2)		11	13	nC
Gate-Source Charge	Q_{GS}			4.4		nC
Gate-Drain Charge	Q_{GD}			1.3		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_{\text{SD}} = 2.0\text{ A}$			1.4	V
Continuous Drain-Source Current	I_{SD}				2.0	A
Pulsed Drain-Source Current	I_{SM}				8.0	A

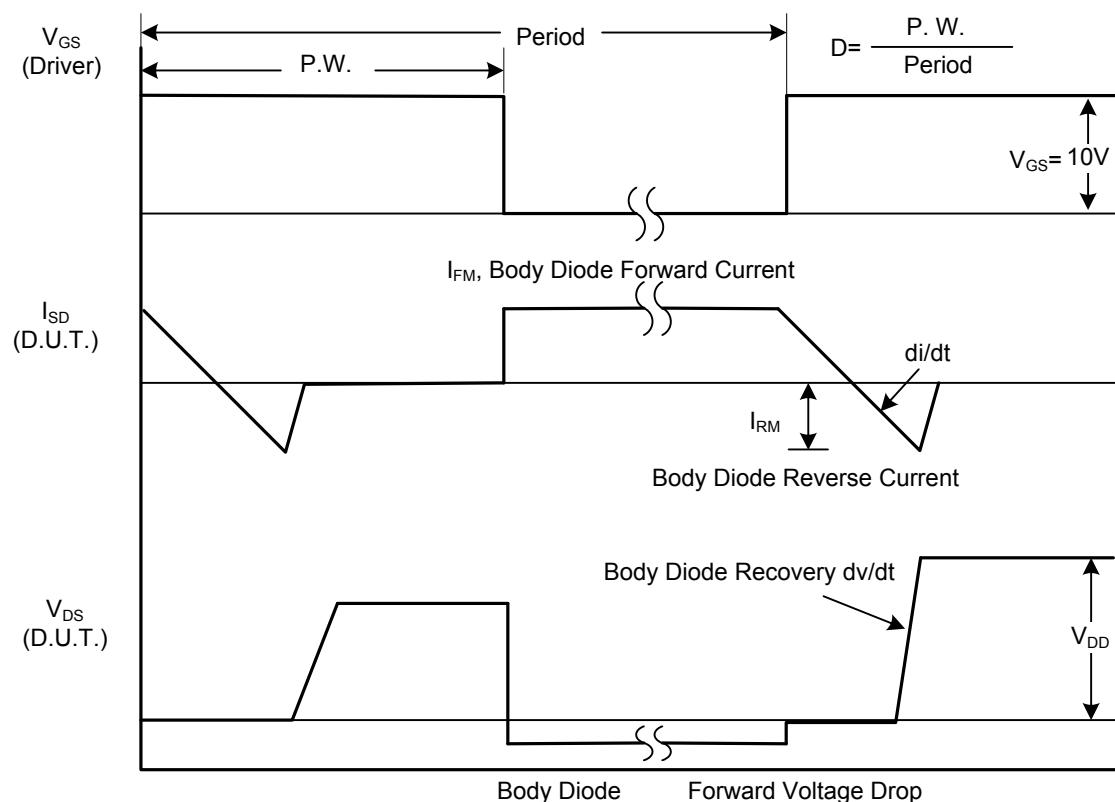
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

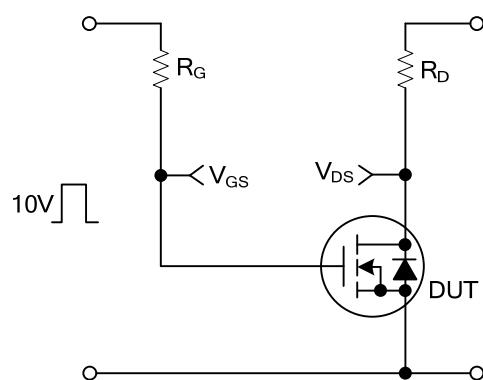


Peak Diode Recovery dv/dt Test Circuit

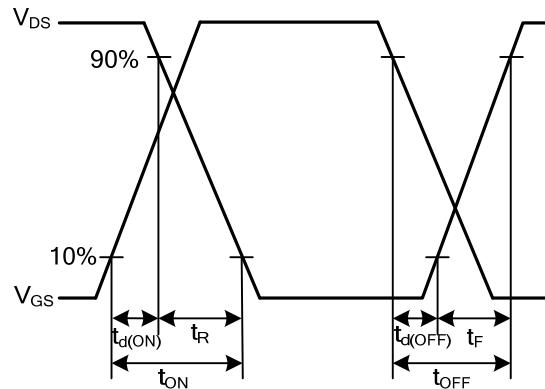


Peak Diode Recovery dv/dt Waveforms

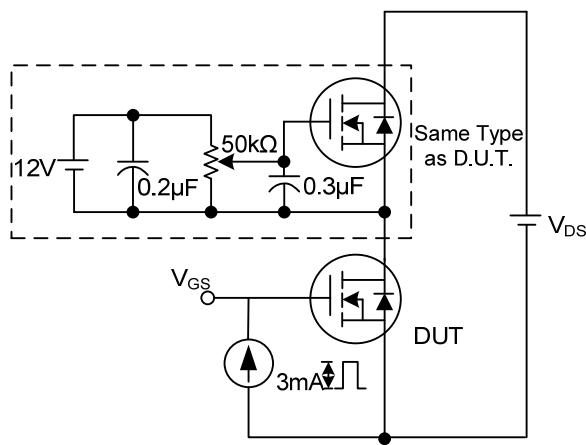
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



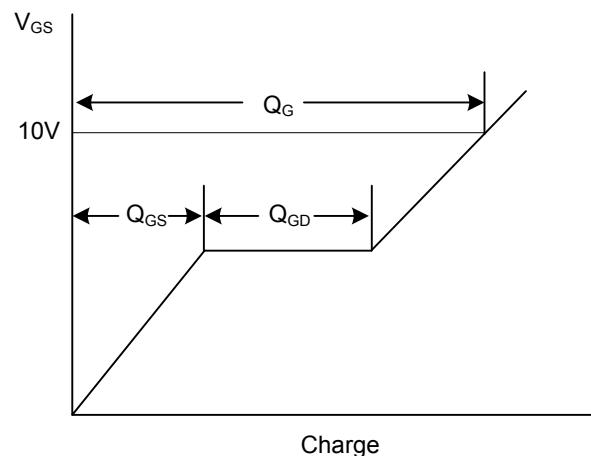
R-Switching Test Circuit



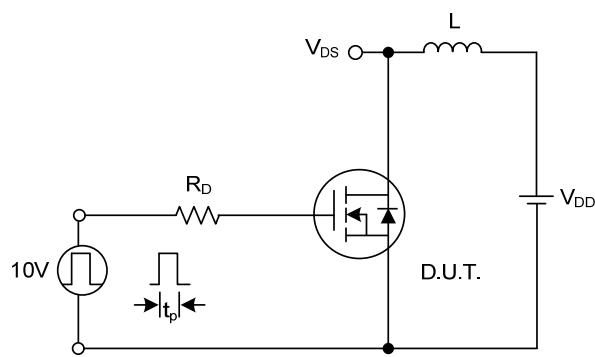
Switching Waveforms



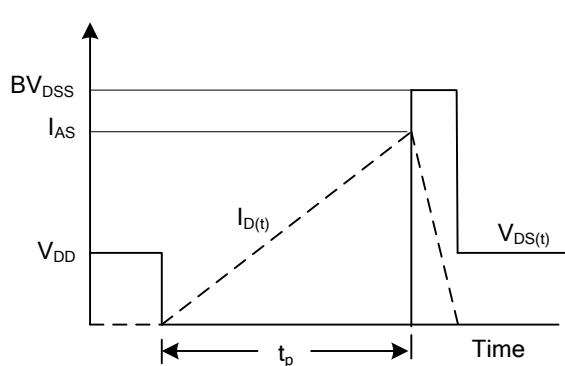
Gate Charge Test Circuit



Gate Charge Waveform

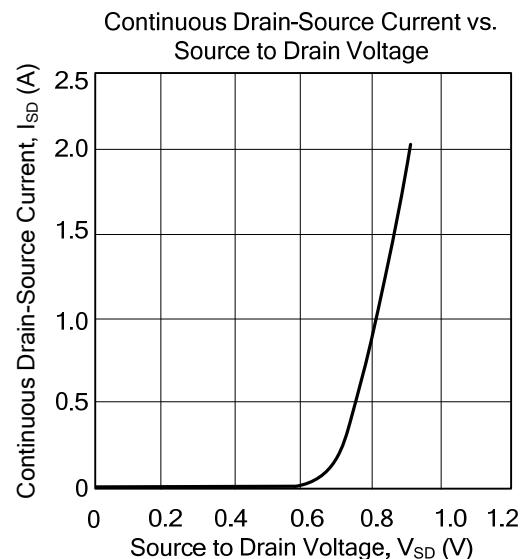
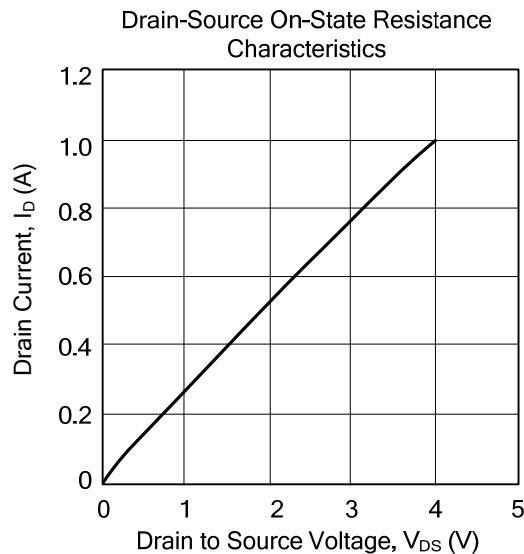
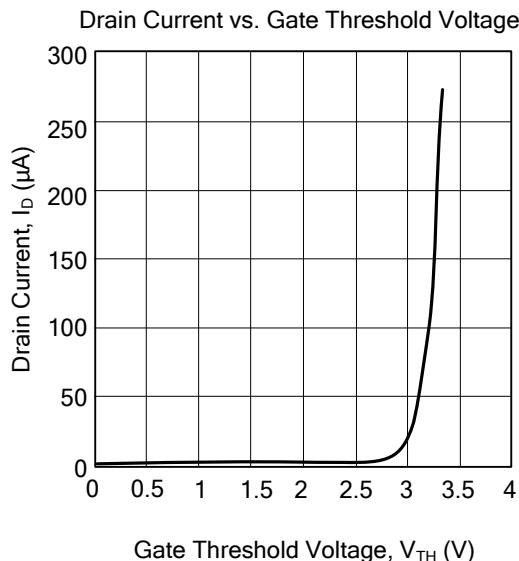
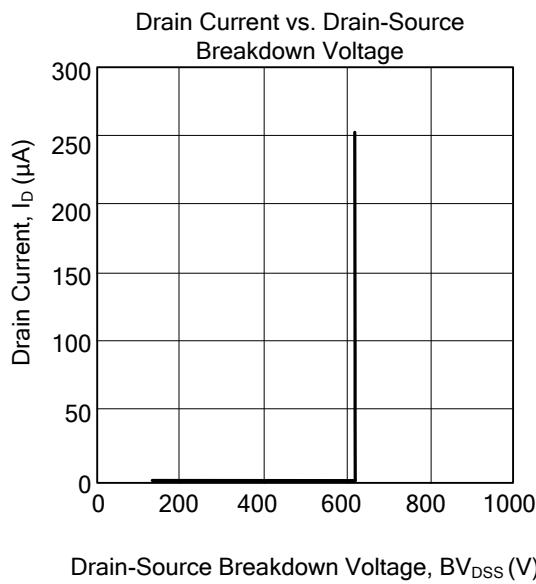


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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